

Voltage Output, High or Low-Side Measurement, Bi-Directional Zero-Drift Series Current Shunt Monitor

■ Features

- Supply voltage: 3 V to 40 V
- Common-mode voltage: -0.1 V to 75 V
- Low quiescent current: 450 μ A (typ)
- High accuracy:
 - Low offset voltage of ± 0.1 mV (max)
 - $\pm 0.8\%$ max total output error
- Gain: 50 V/V
- High slew rate: 3 V/ μ s
- -3 dB bandwidth: 100 kHz
- Operating temperature: -40°C to 125°C

■ Applications

- Electric power steering (EPS) systems
- Body control modules
- Brake systems
- Electronic stability control (ESC) systems

■ Package Information

Part Number	Package	Body Size
DIO2213	DFN-6	2 mm $\times$ 2 mm
	SOIC-8	4.9 mm $\times$ 3.9 mm

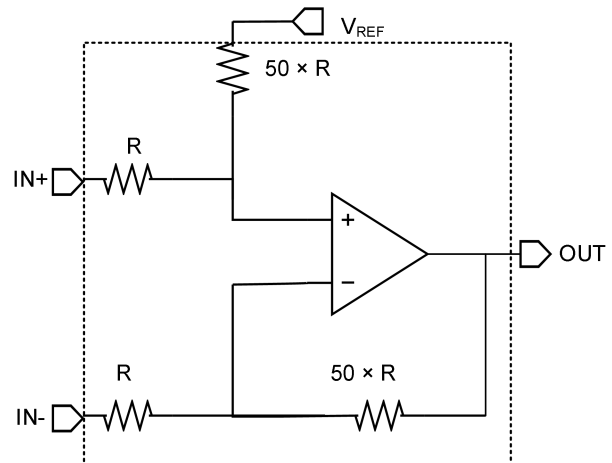
■ Description

The DIO2213 is a high-side current-sense amplifier with voltage output and can sense drops across shunts at common-mode voltage from -0.1 V to 75 V. The gain is 50 V/V, with the according bandwidths of 100 kHz.

The DIO2213 has a maximum offset voltage of only ± 0.1 mV. The DIO2213 total output error is as low as 0.8% over temperature, which greatly improves the accuracy and simplifies the design of system.

The DIO2213 operates from single 3 V to 40 V supply under -40°C to 125°C, with a maximum supply current of 620 μ A.

■ Simplified Schematic



Ordering Information

Ordering Part No.	Top Marking	MSL	RoHS	T _A	Package	
DIO2213CD6	BB1C	3	Green	-40 to 125°C	DFN2*2-6	Tape & Reel, 3000
DIO2213CS8	DIOBB1C	3	Green	-40 to 125°C	SOIC-8	Tape & Reel, 2500

If you encounter any issue in the process of using the device, please contact our customer service at marketing@dioo.com or phone us at (+86)-21-62116882. If you have any improvement suggestions regarding the datasheet, we encourage you to contact our technical writing team at docs@dioo.com. Your feedback is invaluable for us to provide a better user experience.

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1. Pin Assignment and Functions

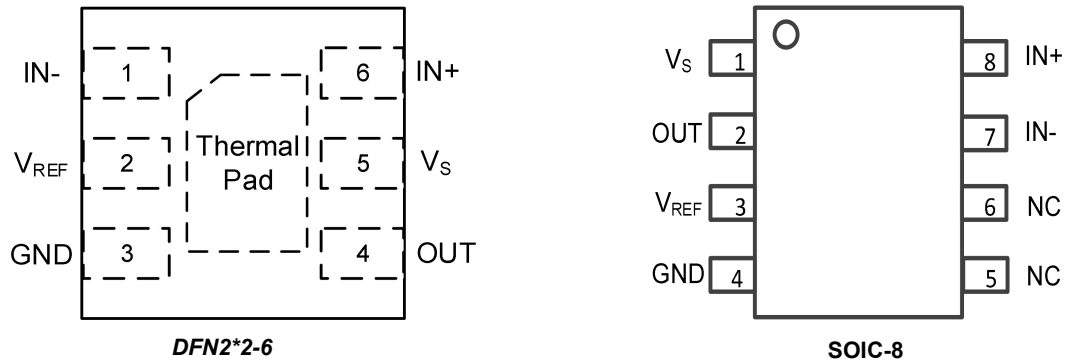


Figure 1. Top view

Name	I/O	Description
IN-	Input	Negative input. Connect to shunt low side
V _{REF}	Input	Reference voltage
GND	-	Ground
OUT	Output	Output voltage of the amplifier
V _S	-	Power supply
IN+	Input	Positive input. Connect to shunt high side
Thermal pad	-	Recommend to connect to the GND plane for improved thermal performance.
NC	-	Not connected

2. Absolute Maximum Ratings

Exceeding the maximum ratings listed under Absolute Maximum Ratings when designing is likely to damage the device permanently. Do not design to the maximum limits because long-time exposure to them might impact the device's reliability. The ratings are obtained over an operating free-air temperature range unless otherwise specified.

Symbol	Parameter		Rating	Unit
V_S	Supply voltage		3 to 44	V
V_{IN+}, V_{IN-}	Current-shunt monitor analog inputs	Differential ($V_{IN+} \sim V_{IN-}$)	-18 to 18	V
		Common mode ⁽¹⁾	GND - 0.3 to 80	
	Analog output ⁽¹⁾		GND - 0.3 to (V_S) + 0.3	V
	Input current into any pin ⁽¹⁾		5	mA
T_A	Ambient temperature		-40 to 125	°C
T_J	Junction temperature		150	°C
T_{STG}	Storage temperature		-65 to 150	°C

Note:

(1) This voltage may exceed the ratings shown if the current at that pin is limited to 5 mA.

3. Recommended Operating Conditions

Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. The ratings are obtained over an operating free-air temperature range unless otherwise specified.

Symbol	Parameter	Rating	Unit
V_{CM}	Common-mode input voltage	-0.1 to 75	V
V_S	Supply voltage	3 to 40	V
T_A	Ambient temperature	-40 to 125	°C

4. ESD Ratings

When a statically-charged person or object touches an electrostatic discharge sensitive device, the electrostatic charge might be drained through sensitive circuitry in the device. If the electrostatic discharge possesses sufficient energy, damage might occur to the device due to localized overheating.

Model	Standard	Value	Unit
Human-body model	ANSI/ESDA/JEDEC JS-001	±2000	V

5. Thermal Considerations

The thermal resistance determines the heat insulation property of a material. The higher the thermal resistance is, the lower the heat loss. Accumulation of heat energy degrades the performance of semiconductor components.

Symbol	Parameter	Value		Unit
		SOIC-8	DFN2*2-6	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	130	TBD	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	50	TBD	°C/W

6. Electrical Characteristics

The values are obtained under these conditions unless otherwise specified: The values are obtained under these conditions unless otherwise specified: $T_A = 25^\circ\text{C}$, $V_S = 12\text{ V}$, $V_{CM} = 12\text{ V}$, $V_{SENSE} = 100\text{ mV}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Input						
V_{SENSE}	Sense input voltage in full-scale	$V_{SENSE} = V_{IN+} - V_{IN-}$		0.15	$(V_S - 0.25)/G$	V
V_{CM}	Common-mode input range	$T_A = -40^\circ\text{C}$ to 125°C	-0.1		75	V
CMR	Common-mode rejection	$V_{IN+} = 0$ to 80 V	80	100		dB
V_{OS}	Offset voltage, RTI	$T_A = 25^\circ\text{C}$		±20	±50	μV
		$T_A = -40^\circ\text{C}$ to 125°C			±100	μV
dV_{OS}/dT	Offset voltage, RTI, versus temperature	$T_A = -40^\circ\text{C}$ to 125°C		0.3		μV/°C
PSR	Offset voltage, RTI, versus power supply	$V_{OUT} = 2\text{ V}$, $V_{IN+} = 18\text{ V}$, 2.7 V , $T_A = -40^\circ\text{C}$ to 125°C		±20		μV/V
I_B	Input bias current, V_{IN-} pin	$T_A = -40^\circ\text{C}$ to 125°C		±220		μA
Output ($V_{SENSE} \geq 20\text{ mV}$)						
G	Gain			50		V/V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
	Total output error ⁽¹⁾	$V_{SENSE} = 120 \text{ mV}$, $V_S = 16 \text{ V}$, $T_A = -40^\circ\text{C}$ to 125°C		± 0.4	± 0.8	%
C_{LOAD}	Maximum capacitive load	No sustained oscillation		0.5		nF
Voltage output						
	Output swing to the positive rail ⁽³⁾	$V_{IN-} = 11 \text{ V}$, $V_{IN+} = 12 \text{ V}$, $T_A = -40^\circ\text{C}$ to 125°C		$V_S - 0.12$	$V_S - 0.25$	V
	Output swing to GND ⁽²⁾	$V_{IN-} = 0 \text{ V}$, $V_{IN+} = -0.5 \text{ V}$, $T_A = -40^\circ\text{C}$ to 125°C		6	50	mV
Frequency response						
BW	Bandwidth	$C_{LOAD} = 5 \text{ pF}$		100		kHz
	Phase margin ⁽²⁾	$C_{LOAD} = 500 \text{ pF}$		40		Degrees
SR	Slew rate			3		V/ μs
	Settling time (1%)	$V_{SENSE} = 10 \text{ mV}_{PP}$ to 100 mV_{PP} , $C_{LOAD} = 5 \text{ pF}$		35		μs
Noise, RTI						
	Voltage noise density ⁽²⁾			70		nV/ $\sqrt{\text{Hz}}$
Power supply						
I_Q	Quiescent current	$V_{OUT} = 2 \text{ V}$, no load		450	620	μA

Note:

- (1) Total output error includes effects of gain error, V_{OS} and non-linearity error.
- (2) Guaranteed by design.
- (3) Specifications subject to change without notice.

7. Typical Characteristics

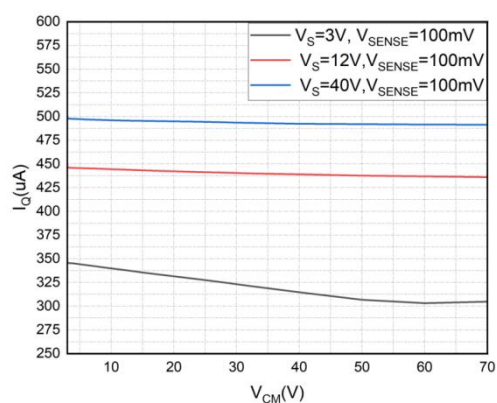


Figure 2. I_Q vs. V_{CM}

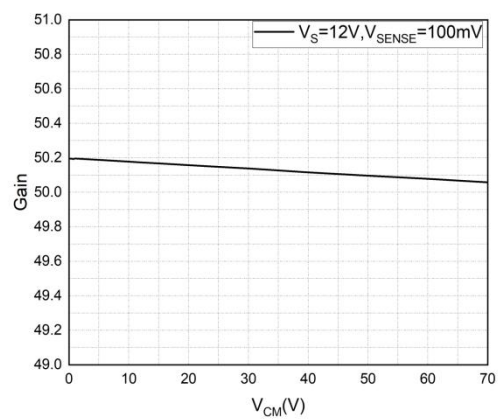


Figure 3. Gain vs. V_{CM}

One possible location for filtering is at the output of the DIO2213 series, in which case the output impedance of the internal buffer increases. Adding a filter at the input pins of the DIO2213 series is a better option although the input impedance makes the input filtering more complicated as shown in Figure 5. To minimize the initial shift in gain and effects of tolerance, use the lowest resistor values. Equation (1) tells the effect on initial gain.

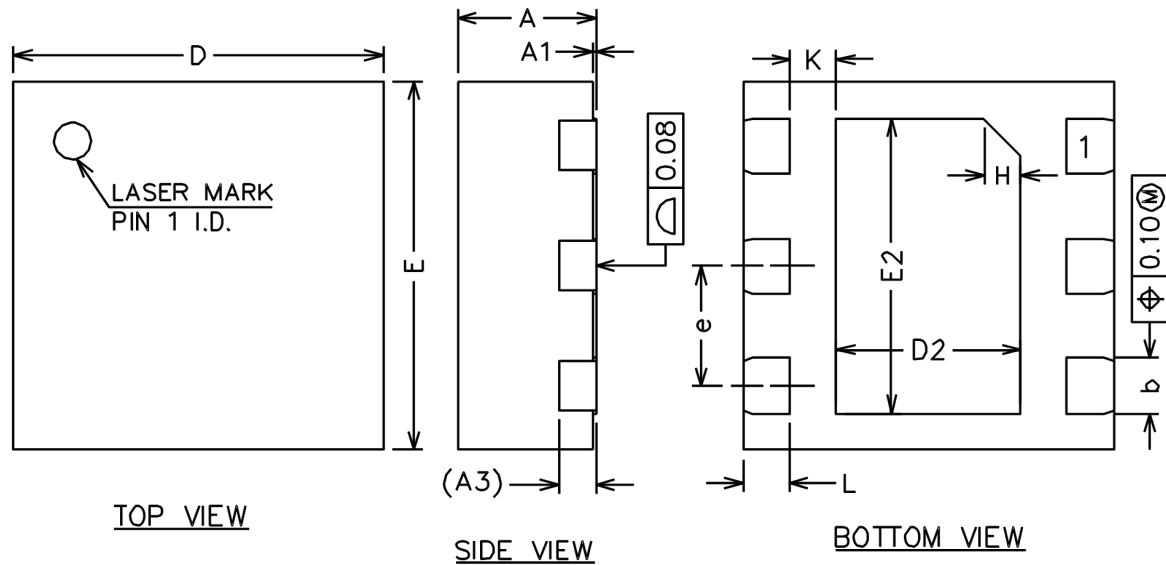
Calculate the total effect on gain error by substituting the 5 k Ω term with 5 k Ω - 30% or 5 k Ω + 30%. Put the tolerance extremes of R_{FILTER} into equation (1). For instance, two resistors of 100 Ω 1% near the input pins, making a gain error of 1.96%. The worst case approach is using an internal 5 k Ω resistor and R_{FILTER} + 3%, which will offer an error gain larger than the normal value.

9. Layout

Use four wire connection, also known as Kelvin connection, to connect the input pins and the sensing resistor together so as to ensure only the current sensing resistance is detected. Inappropriate layout often results in additional resistance between the input pins, causing erroneous measuring. Locate the power-supply bypass capacitor, 0.1 μF recommended, as close as possible to the V_S and GND pins. Use an additional decoupling capacitor to lessen the impacts of noisy or high-impedance power supplies.

10. Physical Dimensions

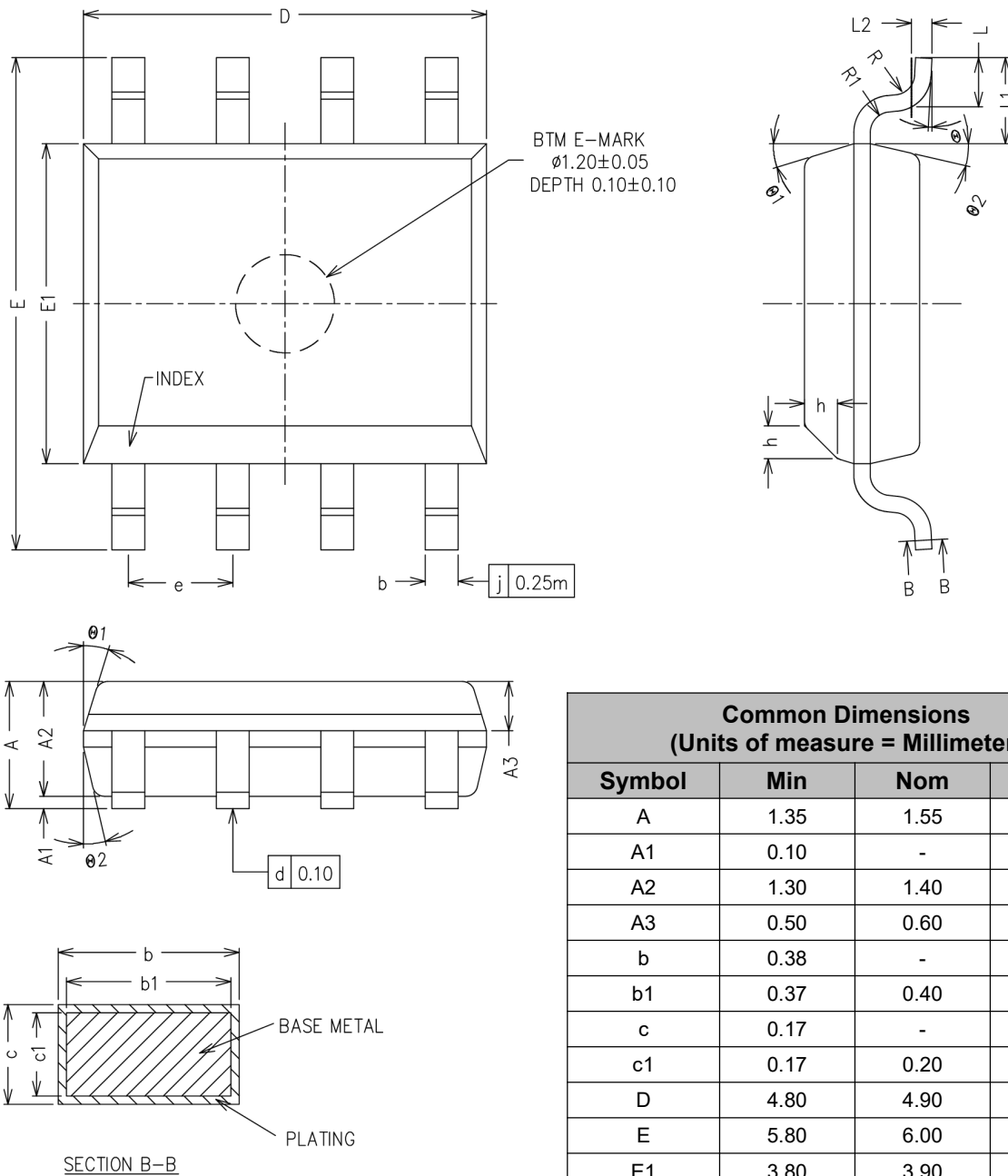
10.1. DFN2*2-6



SIDE VIEW

Common Dimensions (Units of measure = Millimeter)			
Symbol	Min	Nom	Max
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.20 REF		
b	0.25	0.30	0.35
D	1.90	2.00	2.10
E	1.90	2.00	2.10
D2	0.90	1.00	1.10
E2	1.50	1.60	1.70
e	0.55	0.65	0.75
K	0.15	0.25	0.35
L	0.20	0.25	0.30
H	0.20 REF		

10.2. SOIC-8



Common Dimensions (Units of measure = Millimeter)			
Symbol	Min	Nom	Max
A	1.35	1.55	1.75
A1	0.10	-	0.25
A2	1.30	1.40	1.50
A3	0.50	0.60	0.70
b	0.38	-	0.47
b1	0.37	0.40	0.43
c	0.17	-	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
L1	1.04 REF		
L2	0.25 BSC		
R	0.07	-	-
R1	0.07	-	-
h	0.30	0.40	0.50
θ	0°	-	8°
θ_1	15°	17°	19°
θ_2	11°	13°	15°

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